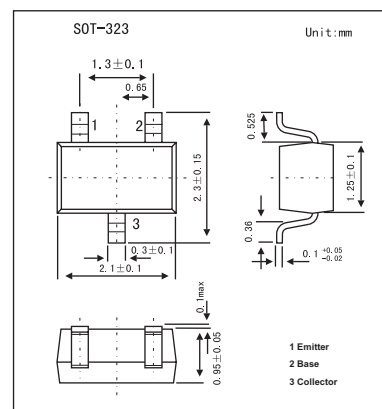


General Purpose Transistor

2SD2351

■ Features

- High DC current gain.
- High emitter-base voltage. ($V_{CBO}=12V$)
- Low saturation voltage.
(Typ. $V_{CE(sat)}=0.3V$ at $I_C/I_B=50mA/5mA$)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	12	V
Collector current	I_C	0.15	A(DC)
		0.2	A(Pulse)*
Collector power dissipation	P_C	0.2	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* Single pulse $P_w=100ms$.

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	$I_C=10\mu A$	60			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C=1mA$	50			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E=10\mu A$	12			V
Collector cutoff current	I_{CBO}	$V_{CB}=50V$			0.3	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=12V$			0.3	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C/I_B=50mA/5mA$			0.3	V
DC current transfer ratio	h_{FE}	$V_{CE}/I_C=5V/1mA$	820		2700	
Output capacitance	f_T	$V_{CE}=5V, I_E=-10mA, f=100MHz$		250		MHz
Transition frequency	C_{ob}	$V_{CB}=5V, I_E=0A, f=1MHz$		3.5		pF

■ h_{FE} Classification

Marking	BJV	BJW
h_{FE}	820~1800	1200~2700